

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	10	davis-matthew.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/31 16:22
S2	0	davis-matthew.in. and lian-lei.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 16:34
S3	0	(davis-matthew.in.) and (lian-lei.in.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 16:35
S4	19	(davis-matthew.in.) or (lian-lei.in.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 16:35
S5	844900	((@ad<="20030411") and ((process) same (control\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 16:38
S6	759	((@ad<="20030411") and ((process) with (control\$3)) and (etch) and (substrate) and ((measur\$4) with (dimension))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:14
S7	53	((@ad<="20030411") and ((process) with (control\$3)) and (etch) and (substrate) and ((measur\$4) with (dimension)) and ((circuit) or (device)) and ((pre-etch) or (post-etch))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 06:12
S8	11	((@ad<="20030411") and ((process) with (control\$3)) and (etch) and (substrate) and ((measur\$4) with (dimension)) and ((circuit) or (device)) and ((pre-etch) and (post-etch))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/27 06:42
S9	0	("60462493").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/27 08:12
S10	2	("5,926,690").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/27 08:15

S11	483	(216/59).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/27 08:19
S12	3916	(438/17).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/27 08:19
S13	2	("20020155629").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 16:22
S14	21	(US-20020155629-\$ or US-20030014144-\$ or US-20030106642-\$ or US-20030165755-\$ or US-20040003896-\$ or US-20040018647-\$ or US-20040029299-\$ or US-20040032592-\$ or US-20040044435-\$ or US-20040078108-\$ or US-20040087041-\$ or US-20040092045-\$ or US-20040092047-\$ or US-20040152221-\$ or US-20040235205-\$).did. or (US-5926690-\$ or US-6567717-\$ or US-6625497-\$ or US-6858361-\$).did. or (US-5926690-\$ or US-20040200574-\$).did.	US-PGPUB; USPAT; DERWENT	OR	ON	2006/02/01 06:59
S15	3	S14 and ((re-work) or (mlti) or (re-process) or (repeat))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 09:12
S16	91	"L2" and ((in-situ) with (chamber))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 09:13
S17	10	"s14" and ((in-situ) with (chamber))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 09:15
S18	21	(US-20020155629-\$ or US-20030014144-\$ or US-20030106642-\$ or US-20030165755-\$ or US-20040003896-\$ or US-20040018647-\$ or US-20040029299-\$ or US-20040032592-\$ or US-20040044435-\$ or US-20040078108-\$ or US-20040087041-\$ or US-20040092045-\$ or US-20040092047-\$ or US-20040152221-\$ or US-20040235205-\$).did. or (US-5926690-\$ or US-6567717-\$ or US-6625497-\$ or US-6858361-\$).did. or (US-5926690-\$ or US-20040200574-\$).did.	US-PGPUB; USPAT; DERWENT	OR	ON	2006/02/01 09:15
S19	0	S18 and ((in-situ) with (chamber))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 09:15

S20	0	S18 and ((in-situ) with (measur\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 09:16
S21	6	S18 and (in-situ)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 09:16
S22	0	((@ad<="20030411") and ((process) with (control\$3)) and (etch) and (substrate) and ((measur\$4) with (dimension)) and ((trench) same (capacitor)) and (polysilicon) and (HBr) and (Cl2))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:16
S23	21	((@ad<="20030411") and (etch) and (substrate) and ((trench) same (capacitor)) and (polysilicon) and (HBr) and (Cl2))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:17
S24	14	((@ad<="20030411") and (etch) and (substrate) and ((trench) same (capacitor)) and (polysilicon) and ((HBr) with (Cl2)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:22
S25	17	((@ad<="20030411") and (etch) and ((trench) same (capacitor)) and (polysilicon) and ((HBr) with (Cl2)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:23